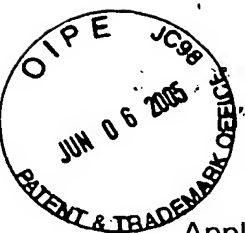


IFW



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Edward Y. CHANG et al. Confirmation No: 4041
Appl. No. : 10/699,839
Filed : November 4, 2003
Title : GROWTH OF GaAs EPITAXIAL LAYERS ON Si SUBSTRATE
BY USING A NOVEL GeSi BUFFER LAYER

TC/A.U. : 2818
Examiner : M. H. C. Tran

Docket No.: : CHAN3228/REF
Customer No: : 23364

RESPONSE TO RESTRICTION REQUIREMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

This is in response to the Official Action of May 6, 2005, in connection with the above identified application.

The Official Action is a restriction requirement in which it is urged that there are two separate and distinct inventions claimed in this application. Applicants elect the Group II invention which includes claims 1-13, without traverse. Applicants reserve the right to file a divisional application on the non-elected invention at a later time.

In view of the election of the Group II invention, without traverse, an early and favorable action on the merits is now believed to be in order and is most respectfully requested.

Respectfully submitted,
BACON & THOMAS, PLLC

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June 6, 2005